

AMENDMENT TO THE CLAIMS:

Please amend the claims as follows. Strikethroughs indicate deletions and underlines indicate additions.

Claim 1 (Currently Amended): Compliant substrate (5, 20, 30) comprising a carrier (1, 14, 21, 31) and at least one thin layer (4, 13, 23, 34) formed on the surface of said carrier and intended to be used as a seed for a hetero-epitaxial growth receive, in integral manner, a stress giving structure, the carrier and the thin layer being joined one to another by joining means (3½, 11, 15, 16½, 24, 25) such that the stresses brought by said structure are absorbed in whole or in part by the thin layer and/or the joining means, characterized in that wherein said joining means comprise at least one joining zone chosen from among the following joining zones is selected from the group consisting of: a layer of microcavities, and/or a bonding interface whose bonding energy is controlled to permit the absorption of said stresses.

Claim 13 (Currently Amended): Compliant substrate according to claim 1, characterized in that said bonding interface with controlled bonding energy is an interface resulting from a controlled by surface preparation and/or an interface resulting from a heat treatment and/or an interface resulting from a creation of defects at this interface.

Claim 14 (Currently Amended): Compliant substrate according to claim 13, characterized in that surface preparation is a control of roughness and/or hydrophiliac.

Claim 15 (Currently Amended): Compliant substrate according to Claim 13, characterized in that said joining zone also comprises at least one intermediate layer (22₁, 32, 33) between the thin layer (23₁, 34) and the carrier (21₁, 31).

Claim 16 (Currently Amended): Compliant substrate according to claim 15, characterized in that the intermediate layer (22₁, 32, 33) is a metal layer or metal alloy layer.

Claim 17 (Currently Amended): Compliant substrate according to claim 15, characterized in that at least one intermediate layer is formed such that it comprises is ~~made up of~~ non-homogeneities able to relax stresses.

Claim 18 (Cancelled)

Claim 19 (Previously Amended): Compliant substrate (5, 20, 30) according to Claim 1, characterized in that said thin layer (4, 13, 23, 34) is in a first crystalline material and is intended to be used as hetero-epitaxial growth seed for a second crystalline material forming said structure.

Claim 20 (Currently Amended): Compliant substrate according to claim 19, characterized in that said thin layer is a pre-stressed layer through the insertion by the presence of a foreign element in said first crystalline material in order to promote the compliance of said substrate.

Claim 21 (Original): Compliant substrate according to claim 20, characterized in that the foreign element is inserted through implantation by bombardment and/or inserted by diffusion.

Claim 22 (Previously Amended): Compliant substrate according to Claim 20, characterized in that said foreign element is a doping agent of the thin layer.

Claim 23 (Previously Amended): Compliant substrate (5, 20, 30) according to Claim 19, characterised in that said first crystalline material is a semiconductor.

Claim 24 (Previously Amended): Application of the compliant substrate (5, 20, 30) according to Claim 19, to the hetero-epitaxial growth of a crystalline material chosen from among GaN, SiGe, AlN, InN, and SiC.

Claim 29 (Previously Added): Compliant substrate according to Claim 14, characterized in that said joining zone also comprises at least one intermediate layer (22; 32, 33) between the thin layer (23; 34) and the carrier (21; 31).

Claim 30 (Cancelled)

Claim 31 (Previously Added): Compliant substrate (5, 20, 30) according to Claim 18, characterized in that said thin layer (4, 13, 23, 34) is in a first crystalline material and

Docket No. 034299-268

is intended to be used as hetero-epitaxial growth seed for a second crystalline material forming said structure.

Claim 32 (Previously Added): Compliant substrate according to Claim 21, characterized in that said foreign element is a doping agent of the thin layer.

Claim 33 (Previously Added): Compliant substrate (5, 20, 30) according to Claim 22, characterized in that said first crystalline material is a semiconductor.

Claim 34 (Previously Added): Application of the compliant substrate (5, 20, 30) according to Claim 23, to the hetero-epitaxial growth of a crystalline material chosen from among GaN, SiGe, AlN, InN and SiC.